

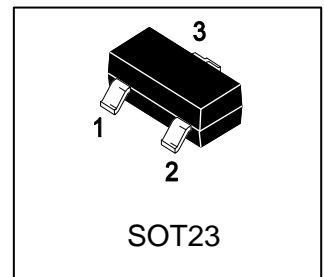
High Voltage Switching Diode

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- AEC-Q101 qualified (Automotive grade with suffix "Q.")
- Exsemi technology

2. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
BAS16	A6	3000/Tape&Reel



3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Continuous Reverse Voltage	VR	75	V
Peak Forward Current	IF	200	mA
Peak Forward Surge Current	IFSM	500	mA

4. THERMAL CHARACTERISTICS

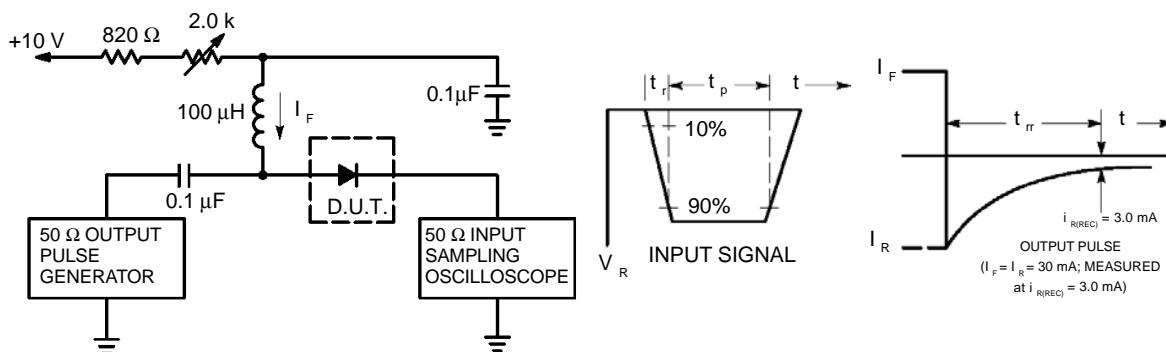
Parameter	Symbol	Limits	Unit
Total Device Dissipation FR-5 Board, (Note 1) TA = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	RθJA	300	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) TA = 25°C Derate above 25°C	PD	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	RθJA	417	°C/W
Junction and Storage Temperature	TJ , Tstg	-55~+150	°C

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

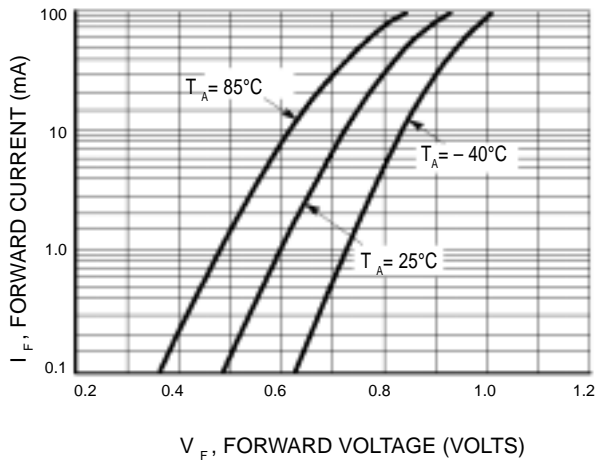
Characteristic	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current ($V_R = 75\text{Vdc}$)	I_R	—	1.0	μAdc
($V_R = 75\text{ Vdc}$, $T_J = 150^\circ\text{C}$)		—	50	
($V_R = 25\text{ Vdc}$, $T_J = 150^\circ\text{C}$)		—	30	
Reverse Breakdown Voltage ($I_{BR} = 100\ \mu\text{Adc}$)	$V_{(BR)}$	75	—	Vdc
Forward Voltage ($I_F = 1.0\ \text{mAdc}$)	V_F	—	715	mV
($I_F = 10\ \text{mAdc}$)		—	855	
($I_F = 50\ \text{mAdc}$)		—	1000	
($I_F = 150\ \text{mAdc}$)		—	1250	
Diode Capacitance ($V_R = 0$, $f = 1.0\ \text{MHz}$)	C_D	—	2.0	pF
Forward Recovery Voltage ($I_F = 10\ \text{mAdc}$, $t_r = 20\text{ns}$)	V_{FR}	—	1.75	Vdc
Reverse Recovery Time ($I_F = I_R = 10\ \text{mAdc}$, $R_L = 50\ \Omega$)	t_{rr}	—	6.0	ns
Stored Charge ($I_F = 10\ \text{mAdc}$ to $V_R = 5.0\text{Vdc}$, $R_L = 500\ \Omega$)	Q_S	—	45	pC



- Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 30 mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 30 mA.
 3. $t_p \gg t_{rr}$

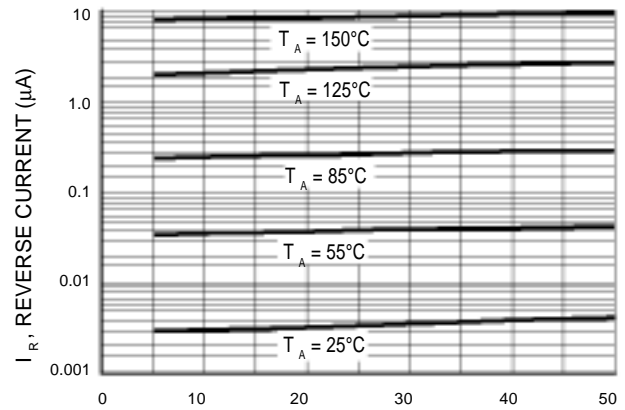
Figure 1. Recovery Time Equivalent Test Circuit

6.ELECTRICAL CHARACTERISTICS CURVES



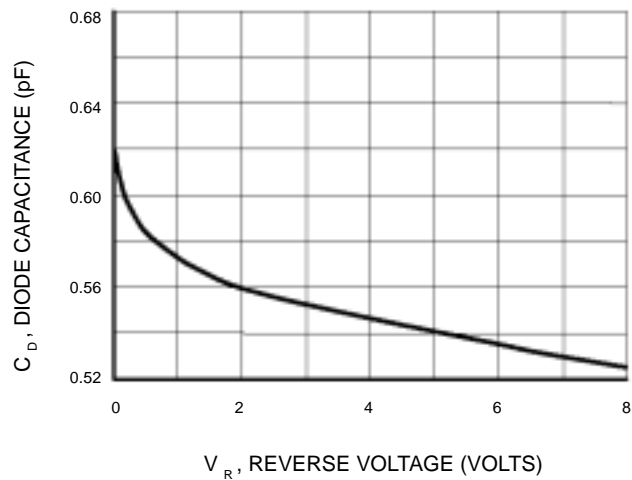
V_F , FORWARD VOLTAGE (VOLTS)

Figure 2. Forward Voltage



V_R , REVERSE VOLTAGE (VOLTS)

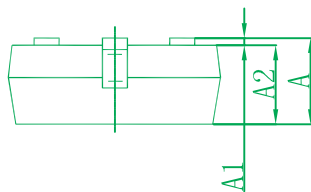
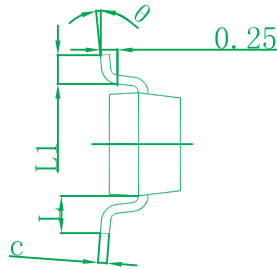
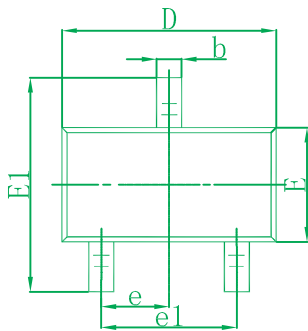
Figure 3. Leakage Current



V_R , REVERSE VOLTAGE (VOLTS)

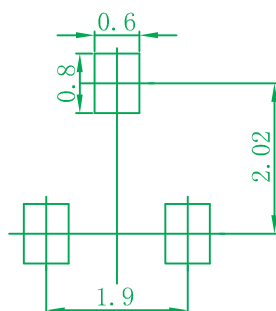
Figure 4. Capacitance

7.OUTLINE AND DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.150	0.035	0.045
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.050	0.110	0.120
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

8.SOLDERING FOOTPRINT



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.